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NTE30049 & NTE30050 Infrared Photo Diode

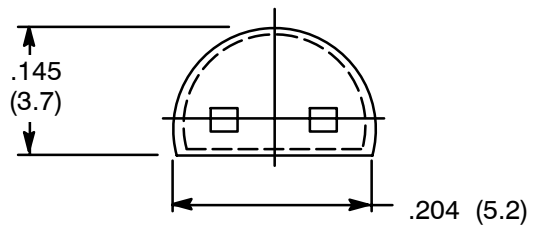
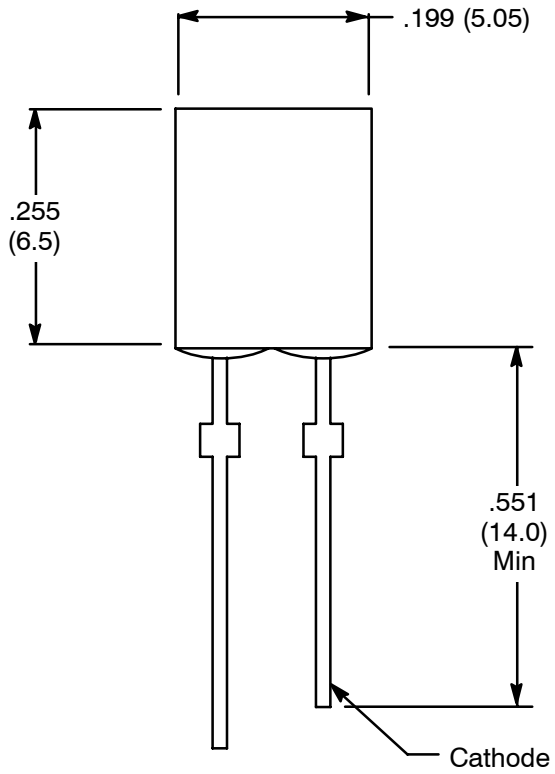
Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Active Area, AA 7.16mm
 Reverse Voltage, V_R 33V
 Power Dissipation, P_D 150mW
 Operating Temperature Range, T_{opr} -25° to $+85^\circ\text{C}$
 Storage Temperature Range, T_{stg} -40° to $+100^\circ\text{C}$
 Lead Temperature (During Soldering, .078 (2mm) from case bottom, 5sec max), T_L $+260^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 100 \text{ mA}$	-	1.3	1.6	V
Half Power NTE30049	2 θ 1/2	$E = 0.5 \text{ mW/cm}$	-	120	-	Degree
NTE30050			-	140	-	Degree
Open Circuit Voltage	V_{OC}	$E = 0.5 \text{ mW/cm}$	-	350	-	mV
Light Current NTE30049	I_p	$E = 0.5 \text{ mW/cm}, V_R = 10\text{V}$	-	20	-	μA
NTE30050			-	17	-	μA
Dark Current	I_R	$V_R = 10\text{V}, E = 0$	-	-	30	nA
Peak Wavelength	λ_p		-	900	-	nm
Sensitivity Wavelength NTE30049	S_λ		500	-	1100	-
NTE30050			760	-	1000	-
Rise Time	t_r	$V_R = 10\text{V}, R_L = 1\text{k}\Omega$	-	45	-	ns
Fall Time	t_f	$V_R = 10\text{V}, R_L = 1\text{k}\Omega$	-	45	-	ns

NTE30049



NTE30050

